



STGD10NC60S STGP10NC60S

10 A, 600 V fast IGBT

Features

- Optimized performance for medium operating frequencies up to 5 kHz in hard switching
- Low on-voltage drop ($V_{CE(sat)}$)

Application

- Motor drive

Description

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

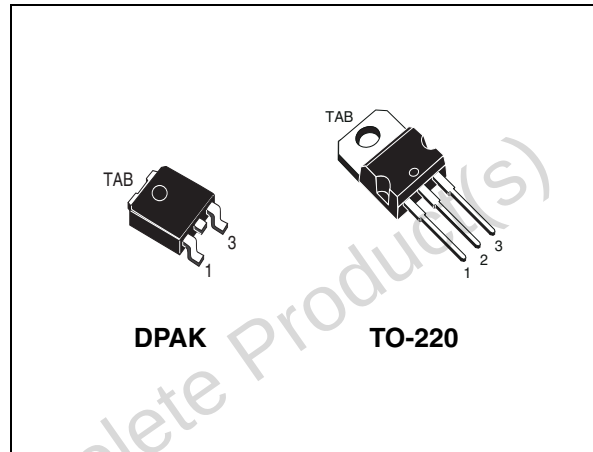


Figure 1. Internal schematic diagram

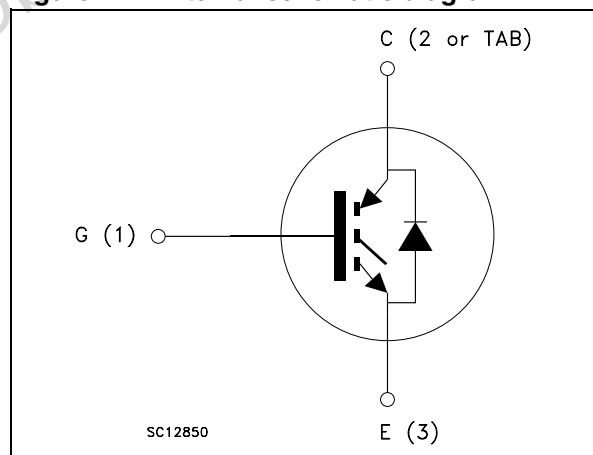


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGD10NC60ST4	GD10NC60S	DPAK	Tape and reel
STGP10NC60S	GP10NC60S	TO-220	Tube

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves)	5
3	Test circuits	8
4	Package mechanical data	9
5	Packaging mechanical data	14
6	Revision history	17

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		DPAK	TO-220	
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$)	600		V
$I_C^{(1)}$	Continuous collector current at $T_C = 25^\circ\text{C}$	18	21	A
$I_C^{(1)}$	Continuous collector current at $T_C = 100^\circ\text{C}$	10	11	A
$I_{CL}^{(2)}$	Turn-off latching current	14		A
$I_{CP}^{(3)}$	Pulsed collector current	25		A
V_{GE}	Gate-emitter voltage	± 20		V
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	60	62.5	W
T_j	Operating junction temperature	-55 to 150		$^\circ\text{C}$

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

2. $V_{clamp} = 80\%(V_{CES})$, $T_j = 150^\circ\text{C}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$

3. Pulse width limited by maximum junction temperature and turn-off within RBSOA

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		DPAK	TO-220	
R_{thJC}	Thermal resistance junction-case	2.08	2	$^\circ\text{C/W}$
R_{thJA}	Thermal resistance junction-ambient	100	62.5	$^\circ\text{C/W}$

2 Electrical characteristics

$T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 1\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 5\text{ A}$ $V_{GE} = 15\text{ V}$, $I_C = 5\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		1.45 1.45	1.65	V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	3.75		5.75	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 600\text{ V}$ $V_{CE} = 600\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$			150 1	μA mA
I_{GES}	Gate-emitter leakage ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{ V}$			± 100	nA
g_{fs}	Forward transconductance	$V_{CE} = 15\text{ V}$, $I_C = 5\text{ A}$		3.5		S

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies} C_{oes} C_{res}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$	-	365 44 8	-	pF pF pF
Q_g Q_{ge} Q_{gc}	Total gate charge Gate-emitter charge Gate-collector charge	$V_{CE} = 480\text{ V}$, $I_C = 5\text{ A}$, $V_{GE} = 15\text{ V}$ <i>Figure 16</i>	-	18 8 3.5	-	nC nC nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$ $R_G = 10\text{ }\Omega$, $V_{GE} = 15\text{ V}$, <i>Figure 17</i>	-	19 4 1330	-	ns ns A/ μs
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$ $R_G = 10\text{ }\Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$ <i>Figure 17</i>	-	18 4.5 1000	-	ns ns A/ μs
$t_r(V_{off})$ $t_{d(off)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$, $R_G = 10\text{ }\Omega$, $V_{GE} = 15\text{ V}$, <i>Figure 17</i>	-	100 160 205	-	ns ns ns
$t_r(V_{off})$ $t_{d(off)}$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$, $R_G = 10\text{ }\Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$ <i>Figure 17</i>	-	165 250 310	-	ns ns ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CC} = 480 \text{ V}$, $I_C = 5 \text{ A}$		60		μJ
$E_{off}^{(2)}$	Turn-off switching losses	$R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, Figure 15	-	340	-	μJ
E_{ts}	Total switching losses			400		μJ
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CC} = 480 \text{ V}$, $I_C = 5 \text{ A}$		90		μJ
$E_{off}^{(2)}$	Turn-off switching losses	$R_G = 10 \Omega$, $V_{GE} = 15 \text{ V}$, $T_J = 125^\circ\text{C}$	-	540	-	μJ
E_{ts}	Total switching losses	Figure 15		630		μJ

1. E_{on} is the turn-on losses when a typical diode is used in the test circuit in [Figure 15](#). If the IGBT is offered in a package with a co-pack diode, the co-pack diode is used as external diode. IGBT's and diode are at the same temperature
2. Turn-off losses included also include also the tail of the collector current

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

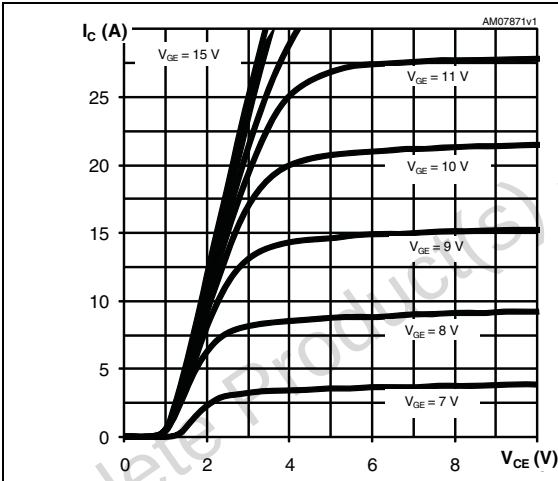


Figure 3. Transfer characteristics

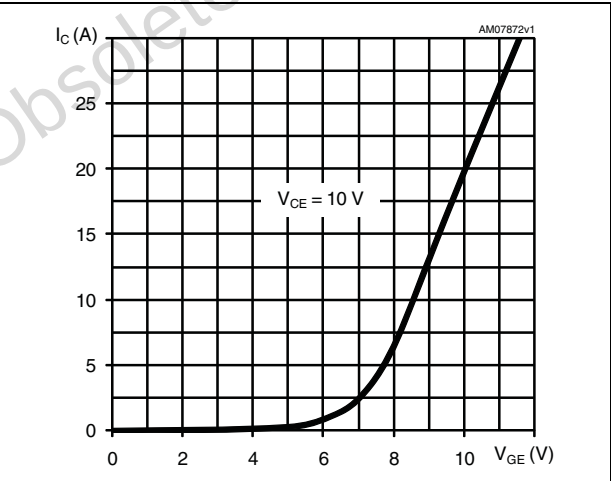


Figure 4. Collector-emitter on voltage vs. collector current

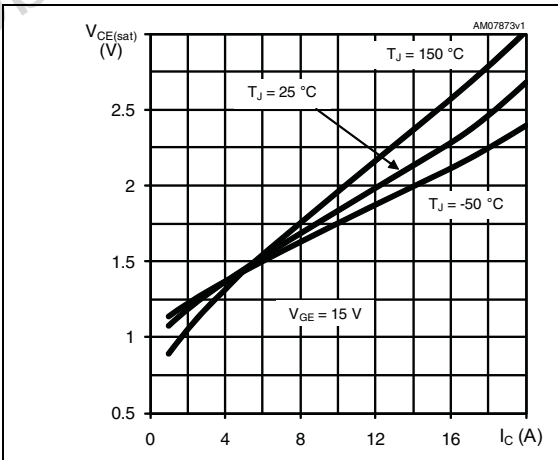


Figure 5. Collector-emitter on voltage vs. temperature

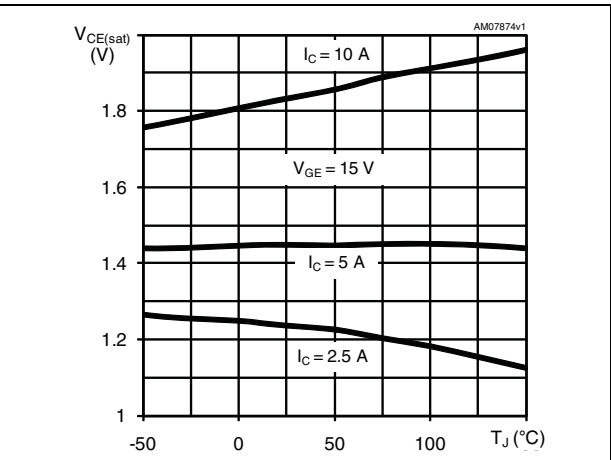


Figure 6. Normalized breakdown voltage vs. temperature

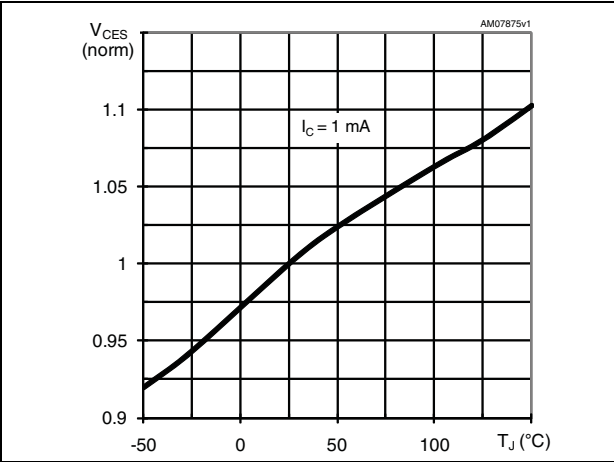


Figure 7. Normalized gate threshold voltage vs. temperature

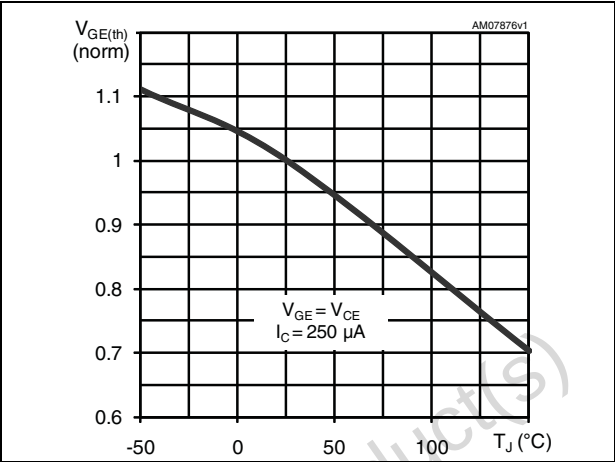


Figure 8. Gate charge vs. gate-emitter voltage

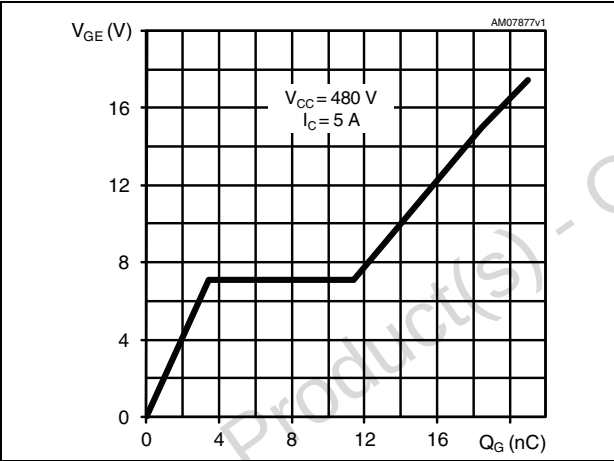


Figure 9. Capacitance variations

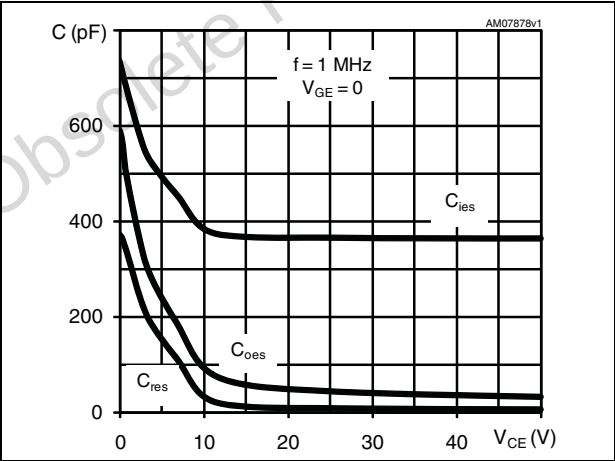


Figure 10. Switching losses vs. temperature

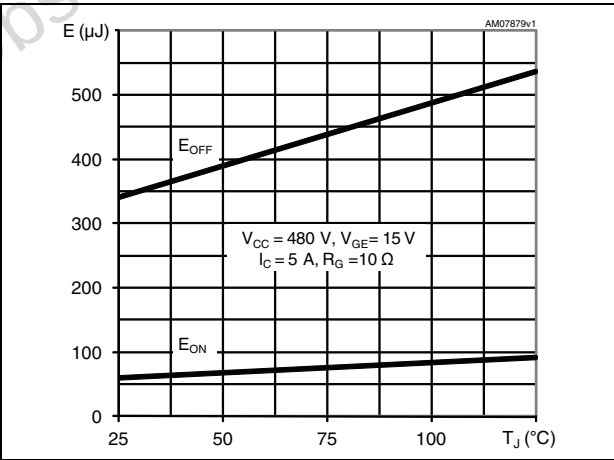


Figure 11. Switching losses vs. gate resistance

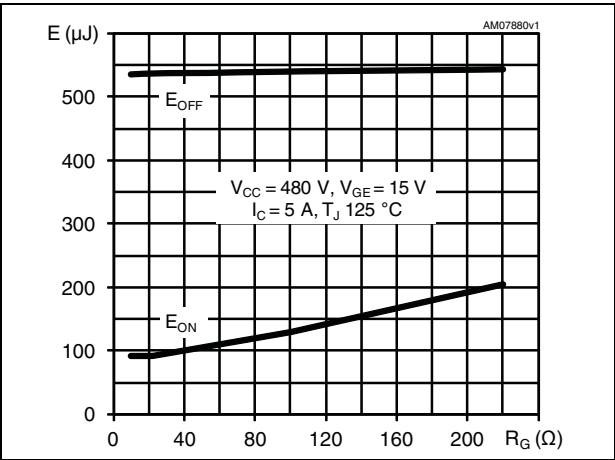


Figure 12. Switching losses vs. collector current

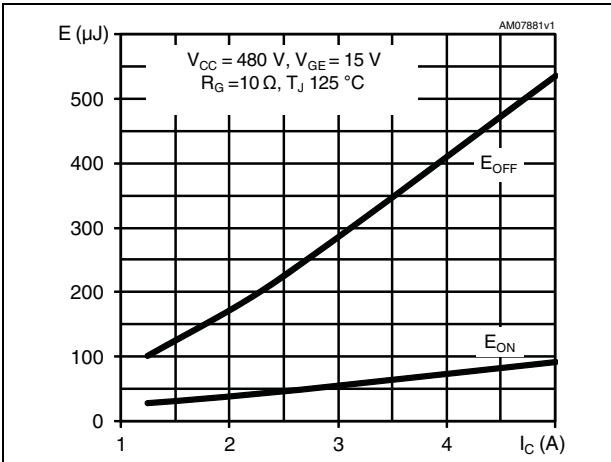


Figure 13. Turn-off SOA

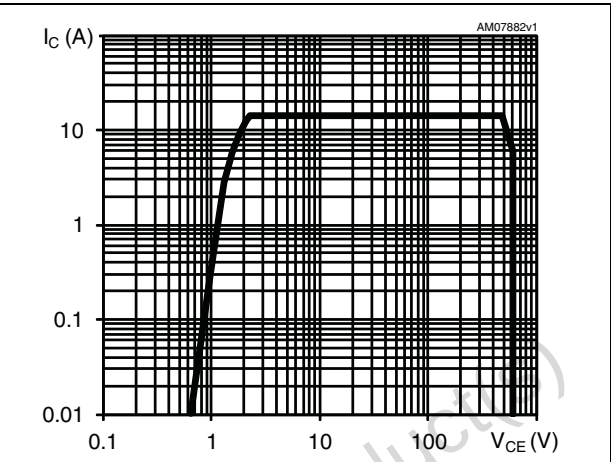
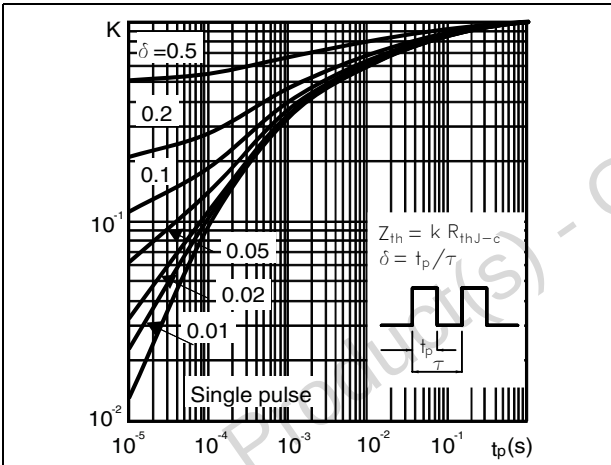


Figure 14. Thermal impedance for DPAK and TO-220



3 Test circuits

Figure 15. Test circuit for inductive load switching

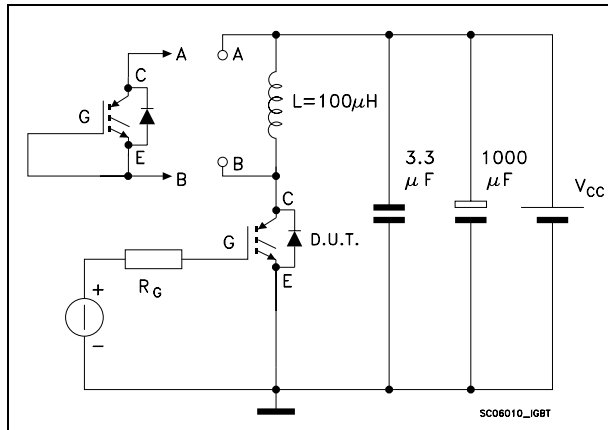


Figure 16. Gate charge test circuit

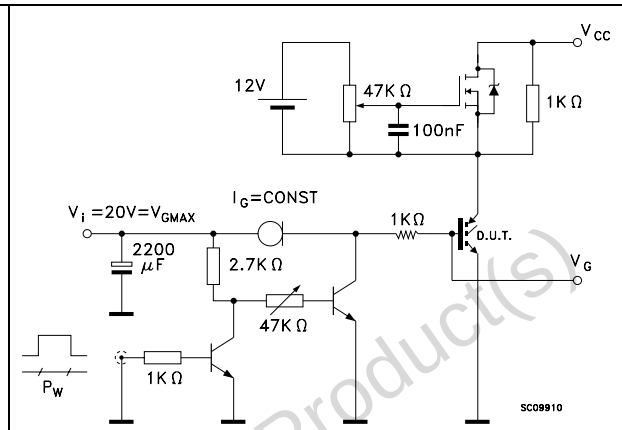
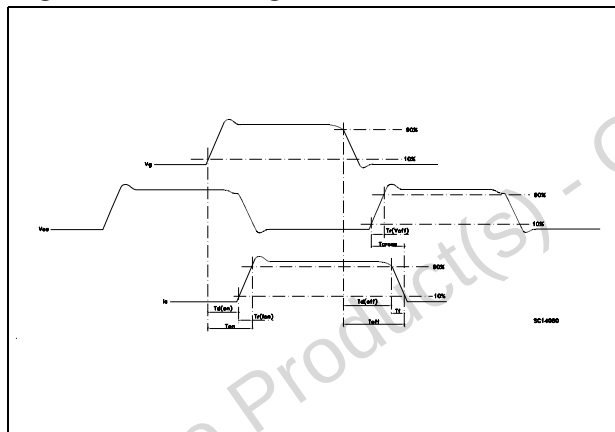


Figure 17. Switching waveforms



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Obsolete Product(s) - Obsolete Product(s)

Table 8. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 18. DPAK (TO-252) drawing

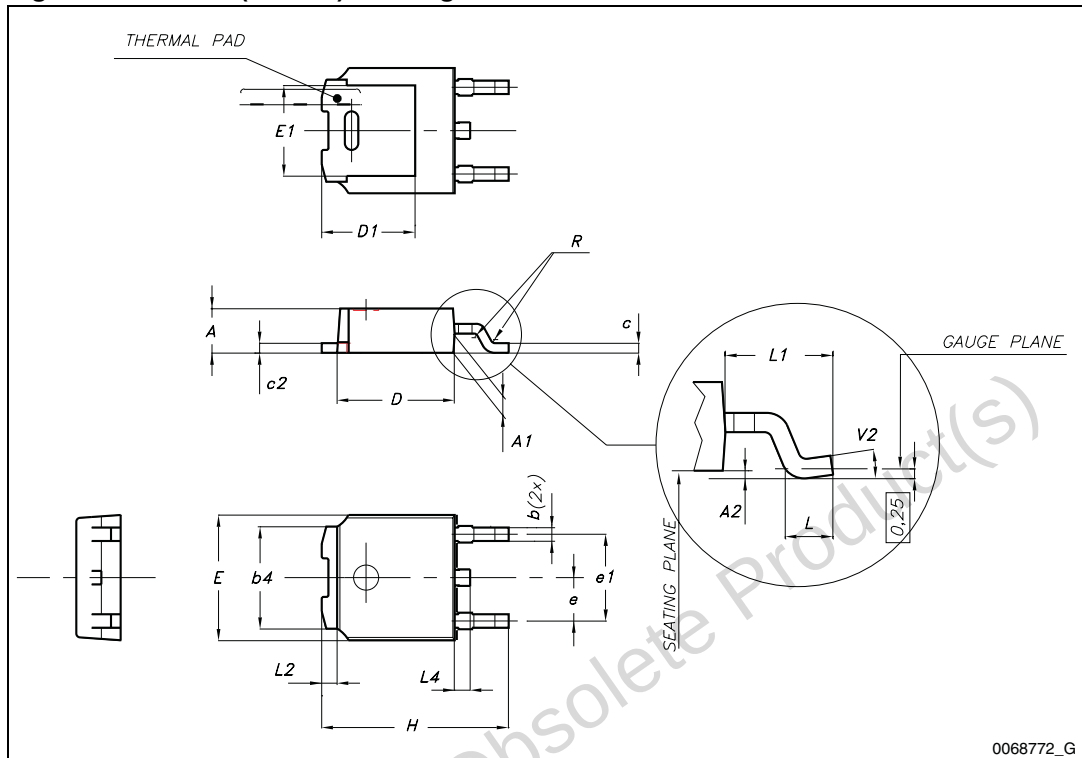
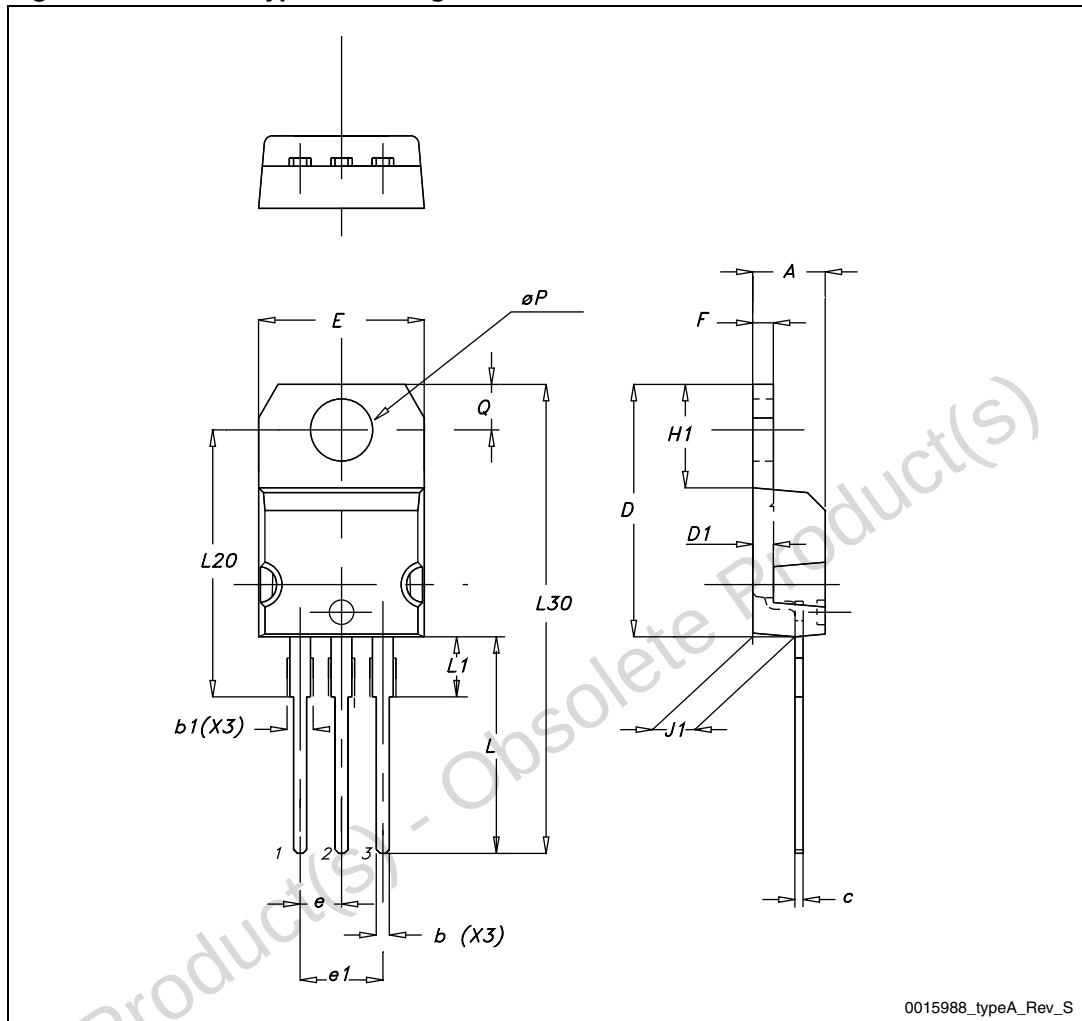


Table 9. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 19. TO-220 type A drawing

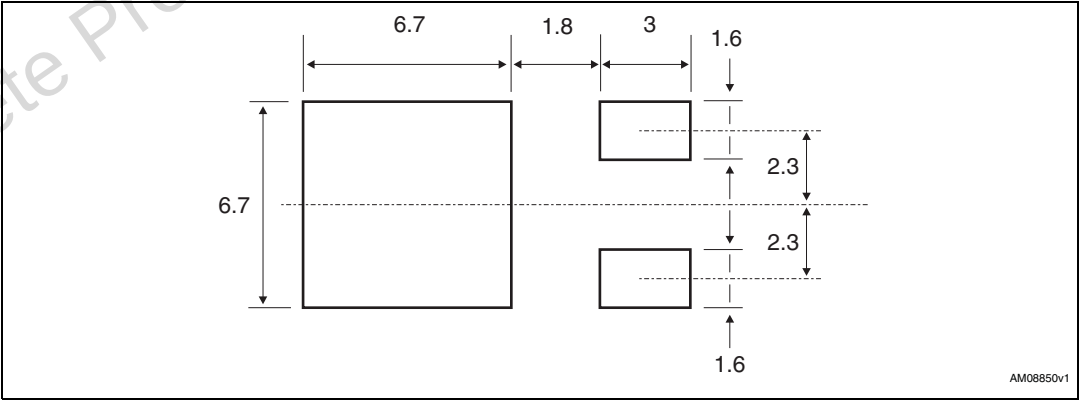


5 Packaging mechanical data

Table 10. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 20. DPAK footprint^(a)



a. All dimension are in millimeters

Figure 21. Tape for DPAK (TO-252)

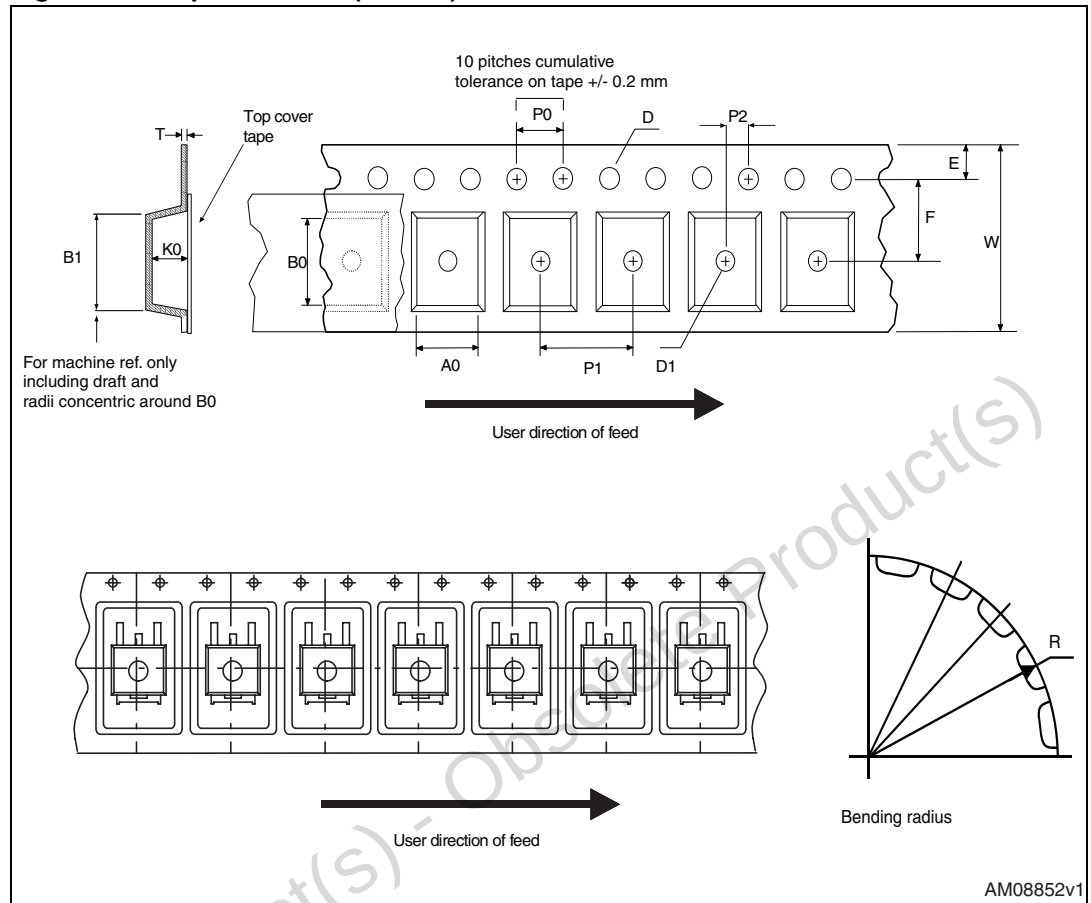
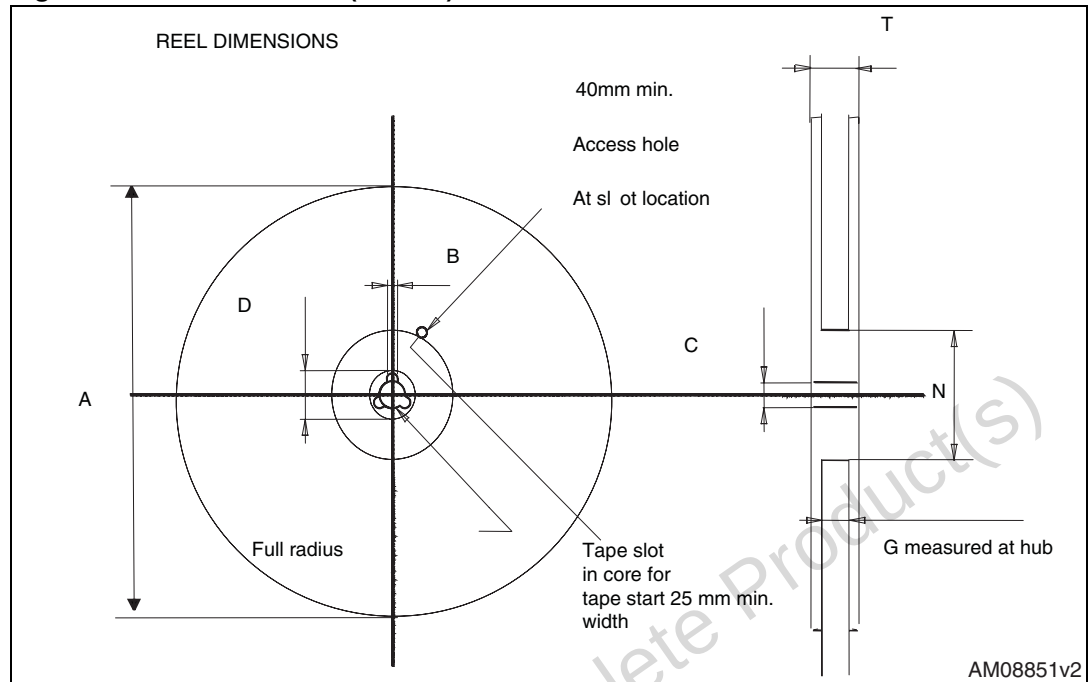


Figure 22. Reel for DPAK (TO-252)

6 Revision history

Table 11. Document revision history

Date	Revision	Changes
06-Jul-2009	1	Initial release
17-Dec-2010	2	Inserted Section 2.1: Electrical characteristics (curves) on page 5

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